



FORM PTO-1449	SERIAL NO. 09/918,853	CASE NO. 10519/29
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE July 30, 2001	GROUP ART UNIT 2812
APPLICANTS: MICHAEL A. VYRODA, N. JOHAN KNALL, and JAMES M. CLEEVES		

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
<i>ZK</i>	A1	5,847,441	12/08/1998	Cutter et al.	—	
<i>ZK</i>	A2	5,913,138	06/15/1999	Yamaoka et al.	—	
<i>ZK</i>	A3	6,185,122	02/06/2001	Johnson et al.	—	
<i>ZK</i>	A4	6,200,837	03/13/2001	lhn et al.	—	

EXAMINER INITIAL	OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)	
<i>ZK</i>	A5	Article, "Plasma-Assisted Oxidation, Anodization, And Nitridation Of Silicon," D.W. Hess, <i>IBM® Journal of Research & Development</i> , Vol. 43, No. ½ - Plasma processing, 1999, [Internet web pages].
<i>ZK</i>	A6	Article, "3D-ROM - A First Practical Step Towards 3D-IC", G. Zhang, Ph.D., <i>Cahners Semiconductor International</i> , July 2000 [Internet web pages].
<i>ZK</i>	A7	Article, "Improving IC Yield with Protective Ceramics", G. Zhang, Ph.D., <i>IBM® Journal of Research & Development</i> , June 2000, pp. 217-220.
<i>ZK</i>	A8	Article, "High-Density Plasma Chemical Vapor Deposition Of Silicon-Based Dielectric Films For Integrated Circuits," <i>IBM® Journal of Research & Development</i> , 1999, S.V. Nguyen, [Internet web pages].
<i>ZK</i>	A9	Article, "Highly Reliable Ultrathin Silicon Oxide Film Formation at Low Temperature by Oxygen Radical Generated in High-Density Krypton Plasma," Sekine et al., <i>IEEE Transactions on Electron Devices</i> , Vol. 48, No. 8, August 2001.
<i>ZK</i>	A10	Article, "A Novel High-Density Low-Cost Diode Programmable Read Only Memory," de Graaf et al., 1996 IEEE, <i>IEDM 96-189-192</i> .

EXAMINER: <i>[Signature]</i>	DATE CONSIDERED: <i>April 16, 2003</i>
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.